

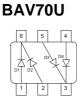
Silicon Switching Diode

- For high-speed switching applications
- Common cathode configuration
- BAV70S / U: For orientation in reel see package information below
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101

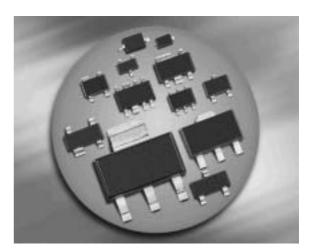


BAV70 BAV70W





BAV70S



Туре	Package	Configuration	Marking	
BAV70	SOT23	common cathode	A4s	
BAV70S	SOT363	double common cathode	A4s	
BAV70U	SC74	double common cathode	A4s	
BAV70W	SOT323	common cathode	A4s	

¹Pb-containing package may be available upon special request



Parameter	Symbol	Value	Unit
Diode reverse voltage	V _R	80	V
Peak reverse voltage	V _{RM}	85	
Forward current	I _F	200	mA
Non-repetitive peak surge forward current	I _{FSM}		A
<i>t</i> = 1 μs		4.5	
<i>t</i> = 1 ms		1	
t = 1 s single		0.5	
t = 1 s double		0.75	
Total power dissipation	P _{tot}		mW
BAV70, <i>T</i> _S ≤ 33°C		250	
BAV70S, <i>T</i> _S ≤ 85°C		250	
BAV70U, <i>T</i> _S ≤ 90°C		250	
BAV70W, <i>T</i> _S ≤ 103°C		250	
Junction temperature	Ti	150	°C
Storage temperature	T _{stq}	-65 150	

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}		K/W
BAV70		≤ 460	
BAV70S		≤ 260	
BAV70U		≤ 240	
BAV70W		≤ 190	

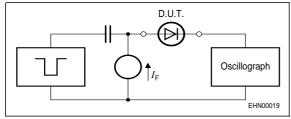
¹For calculation of $R_{\rm thJA}$ please refer to Application Note Thermal Resistance



Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics	-				
Breakdown voltage	V _(BR)	85	-	-	V
<i>I</i> _(BR) = 100 μA					
Reverse current	I _R				μA
<i>V</i> _R = 70 V		-	-	0.15	
$V_{\rm R} = 25 \text{ V}, \ T_{\rm A} = 150 \text{ °C}$		-	-	30	
$V_{\rm R} = 70 \text{ V}, \ T_{\rm A} = 150 \ ^{\circ}{\rm C}$		-	-	50	
Forward voltage	V _F				mV
$I_{\rm F} = 1 {\rm mA}$		-	-	715	
<i>I</i> _F = 10 mA		-	-	855	
<i>I</i> _F = 50 mA		-	-	1000	
<i>I</i> _F = 100 mA		-	-	1200	
<i>I</i> _F = 150 mA		-	-	1250	
AC Characteristics			·		·
Diode capacitance	CT	-	-	1.5	pF
$V_{R} = 0 V, f = 1 MHz$					
Reverse recovery time	<i>t</i> _{rr}	-	-	4	ns
$\mathit{I}_{\rm F}$ = 10 mA, $\mathit{I}_{\rm R}$ = 10 mA, measured at $\mathit{I}_{\rm R}$ = 1mA ,					
$R_{\rm L}$ = 100 Ω					

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

Test circuit for reverse recovery time



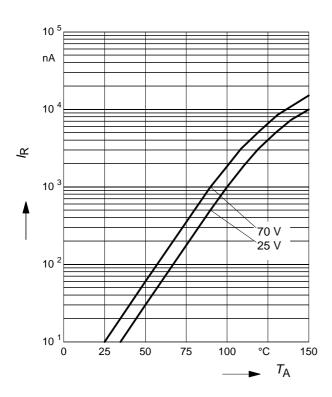
Pulse generator: $t_{\rm p}$ = 100ns, D = 0.05, $t_{\rm r}$ = 0.6ns, $R_{\rm i}$ = 50 Ω

Oscillograph: $R = 50\Omega$, $t_r = 0.35$ ns, C = 0.05pF



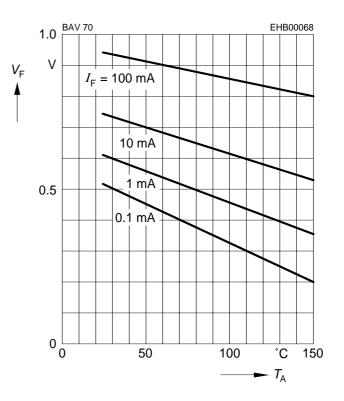
Reverse current $I_{R} = f(T_{A})$

 $V_{\rm R}$ = Parameter



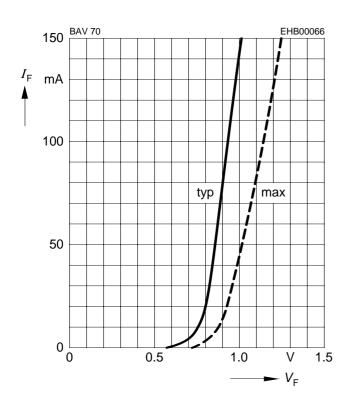
Forward Voltage $V_{\rm F} = f(T_{\rm A})$

 $I_{\rm F}$ = Parameter

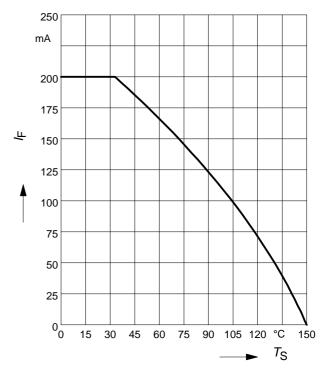


Forward current $I_{\rm F} = f (V_{\rm F})$

 $T_A = 25^{\circ}C$

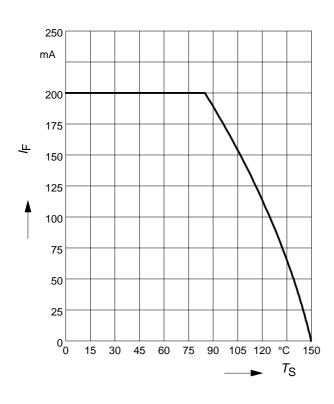


Forward current $I_{\mathsf{F}} = f(T_{\mathsf{S}})$ BAV70

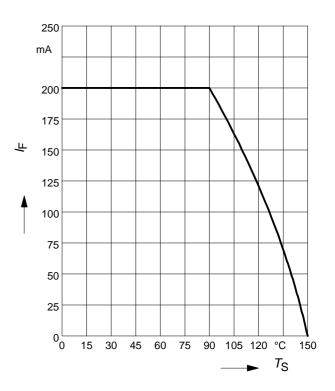




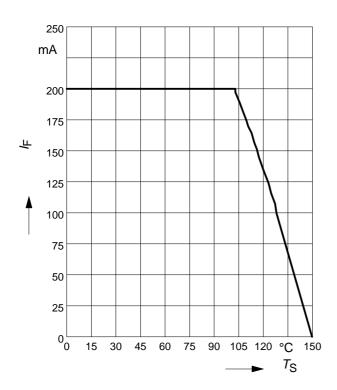
Forward current $I_{\mathsf{F}} = f(T_{\mathsf{S}})$ BAV70S



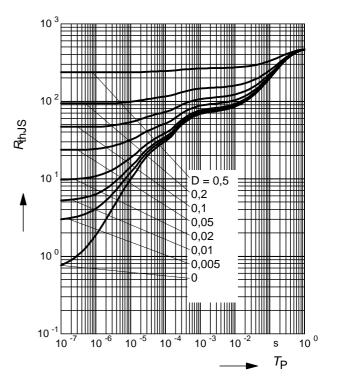
Forward current $I_{\rm F} = f(T_{\rm S})$ BAV70U



Forward current $I_{\mathsf{F}} = f(T_{\mathsf{S}})$ BAV70W

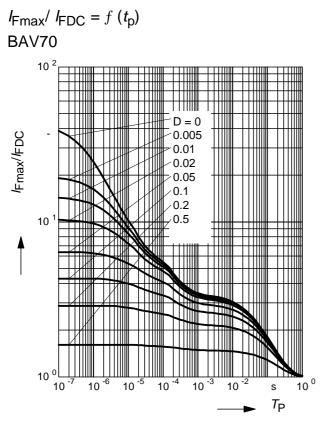


Permissible Puls Load $R_{thJS} = f(t_p)$ BAV70

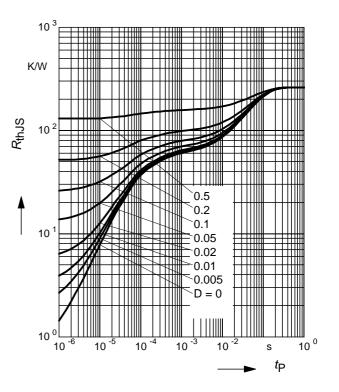




Permissible Pulse Load

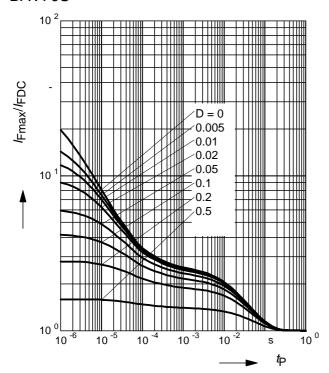


Permissible Puls Load $R_{thJS} = f(t_p)$ BAV70S

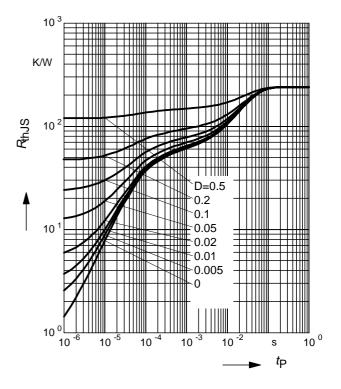


Permissible Pulse Load

 $I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$ BAV70S



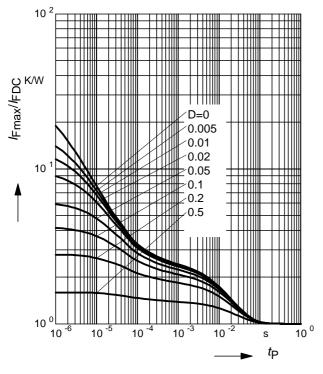
Permissible Puls Load $R_{\text{thJS}} = f(t_{\text{p}})$ BAV70U





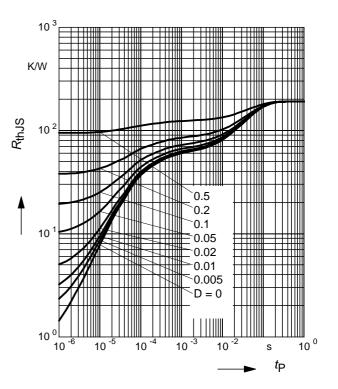
Permissible Pulse Load

$I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$ BAV70U



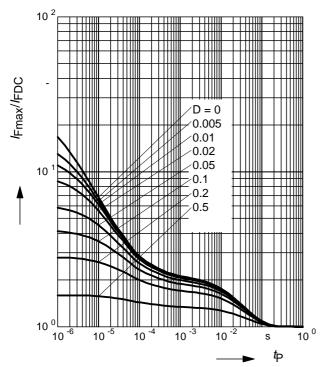
Permissible Puls Load $R_{\text{thJS}} = f(t_{\text{p}})$

BAV70W



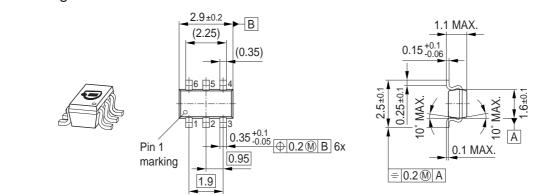
Permissible Pulse Load

 $I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$ BAV70W

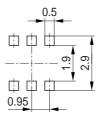




Package Outline

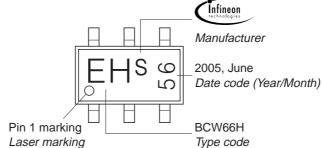


Foot Print



Marking Layout (Example)

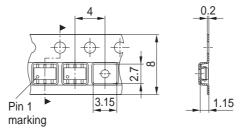
Small variations in positioning of Date code, Type code and Manufacture are possible.



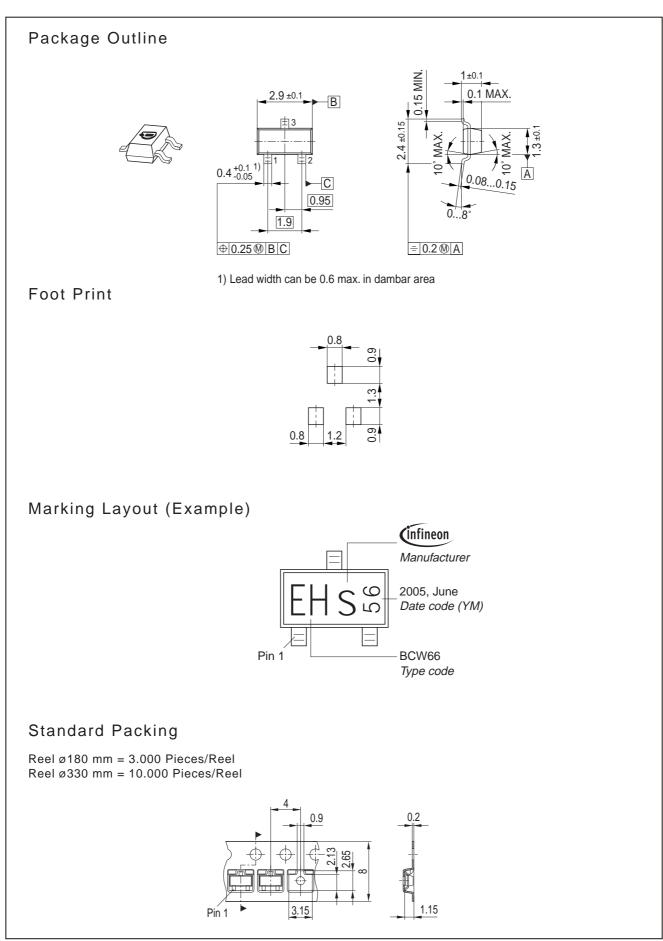
Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

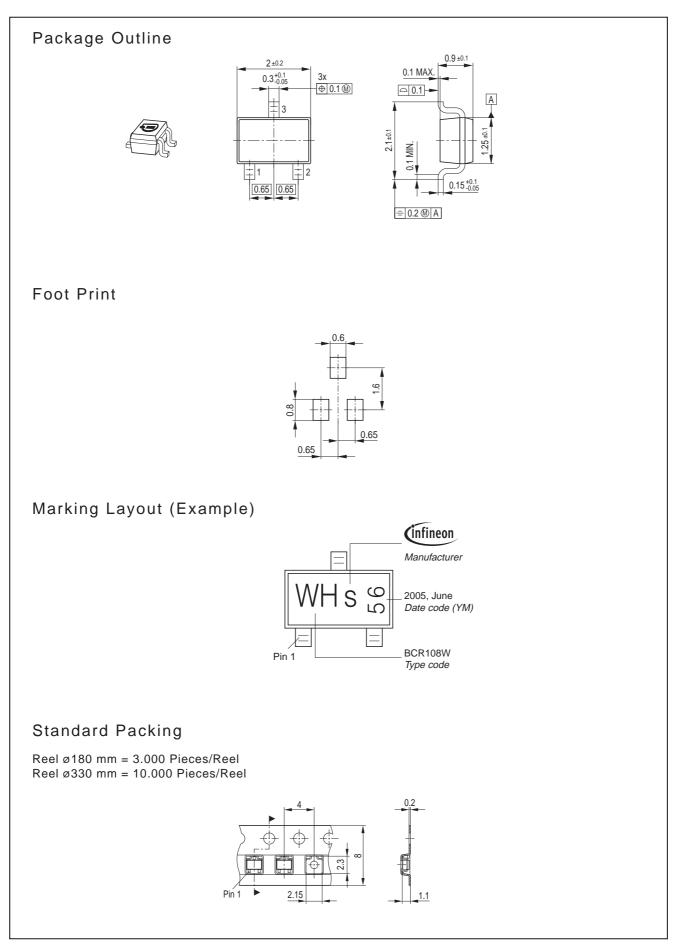
For symmetric types no defined Pin 1 orientation in reel.



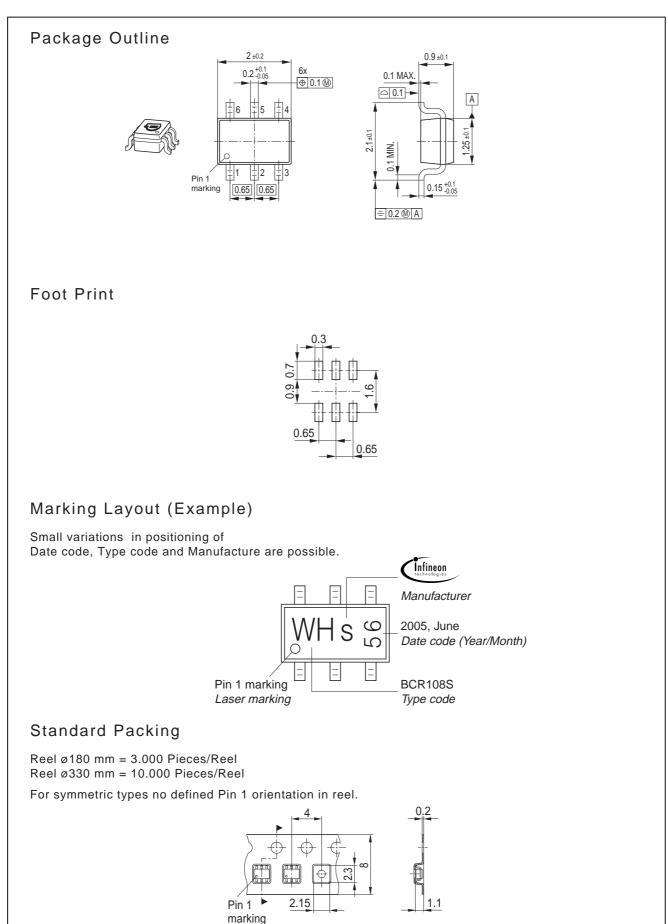














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